

Thin Films Division Fachverband Dünne Schichten (DS)

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Overview of Invited Talks and Sessions

(Lecture rooms: H 2032 and H 2032; Posters: A and F)

Invited Talks

DS 3.1	Mon	15:00–15:30	H 2032	Thin film growth studies using time-resolved X-ray scattering — •STEFAN KOWARIK
DS 9.1	Tue	9:30–10:00	H 2032	Electronic doping of crystalline silicon nanoparticles — •RUI N. PEREIRA
DS 9.3	Tue	10:15–10:45	H 2032	Impurity doping of Si nanocrystals studied by single-quantum-dot spectroscopy — •JAN VALENTA, ILYA SYCHUGOV, JAN LINNROS, MINORU FUJII
DS 9.4	Tue	10:45–11:15	H 2032	Active Silicon Nanovolume Doping: Failure and Alternatives — •DIRK KÖNIG
DS 9.5	Tue	11:30–12:00	H 2032	Doping issues in semiconductor field-effect transistors — •JOACHIM KNOCH
DS 9.6	Tue	12:00–12:30	H 2032	Probing composition and conductivity in 3D-structures and confined volumes. — •WILFRIED VANDERVORST
DS 9.7	Tue	12:30–13:00	H 2032	Silicon Nanowire Devices and Applications — •THOMAS MIKOLAJICK, WALTER WEBER
DS 19.1	Wed	9:30–10:00	H 2032	Ferromagnetic shape memory alloys: From ion-beam assisted synthesis to plasma-aided functionalization for biomedical applications — ARIYAN ARABI-HASHEMI, UTA ALLENSTEIN, FLORIAN SZILLAT, ASTRID WEIDT, MAREIKE ZINK, •STEFAN G. MAYR
DS 19.2	Wed	10:00–10:30	H 2032	Writing magnetic patterns using ion-beams — •RANTEJ BALI
DS 20.1	Wed	9:30–10:00	H 0111	Differential Optical Spectroscopy for Surface Science — •PETER ZEP-PENFELD
DS 20.2	Wed	10:00–10:30	H 0111	<i>In situ</i> Raman monitoring of Potassium intercalation in Manganese Phthalocyanine — •OVIDIU D. GORDAN, MICHAEL LUDEMANN, FRANZISKA LÜTTICH, DMYTRO SOLONENKO, PHILIPP SCHÄFER, DIETRICH R.T. ZAHN
DS 20.3	Wed	10:30–11:00	H 0111	Infrared surface and interface studies - vibrational analysis and beyond — •ANNEMARIE PUCCI
DS 20.4	Wed	11:00–11:30	H 0111	Correlation of IR spectra with thin film structure at solid-water interfaces — •KARSTEN HINRICHS
DS 20.5	Wed	11:30–12:00	H 0111	In-situ characterization of electronic materials by optical second-harmonic generation — •MICHAEL DOWNER
DS 34.1	Thu	9:30–10:00	H 2032	Growth, properties and devices of gallium-oxide-based widegap semiconductors — •SHIZUO FUJUTA
DS 34.6	Thu	11:30–12:00	H 2032	BaSnO₃; The next generation of transparent conducting oxide? — •DAVID SCANLON
DS 37.1	Thu	15:00–15:30	H 2032	Optical properties and band structure of transparent semiconducting oxides — •RÜDIGER GOLDHAHN

DS 37.6	Thu	16:45–17:15	H 2032	Thermodynamic stability and electronic structure of TCO surfaces: A computational approach — •KARSTEN ALBE, PETER AGOSTON, MANUEL DIEHM, ARNO FEY
DS 37.10	Thu	18:00–18:30	H 2032	Synthesis and Stability of Indium (III) Oxide Polymorphs — •ALEKSANDER GURLO, MAGED BEKHEET
DS 40.1	Fri	9:30–10:00	H 2032	From 2D to 1D: Honeycomb crystals and their nanoribbons — •FRIEDHELM BECHSTEDT

Invited talks of the joint symposium SYDW

See SYDW for the full program of the symposium.

SYDW 1.1	Mon	9:30–10:00	H 0105	Domain walls: from conductive paths to technology roadmaps — •GUSTAU CATALAN
SYDW 1.2	Mon	10:00–10:30	H 0105	Domain walls and oxygen vacancies - towards reversible control of domain wall conductance — •PATRYCJA PARUCH
SYDW 1.3	Mon	10:30–11:00	H 0105	Novel mechanisms of domain-wall formation — •ANDRES CANO
SYDW 1.4	Mon	11:30–12:00	H 0105	Novel materials at domain walls — •BEATRIZ NOHEDA
SYDW 1.5	Mon	12:00–12:30	H 0105	Controlling and mapping domain wall behaviour in ferroelectrics — •JOHN MARTIN GREGG, JONATHAN WHYTE, RAYMOND MCQUAID, MICHAEL CAMPBELL, AMIT KUMAR, ROGER WHATMORE

Invited talks of the joint symposium SYMM

See SYMM for the full program of the symposium.

SYMM 1.1	Thu	9:30–10:15	H 0105	From MAX to MXene - From 3D to 2D — •MICHEL BARSOUM
SYMM 1.2	Thu	10:15–10:45	H 0105	Structure evolution during low temperature growth of nanolaminate thin films — •J.M. SCHNEIDER, L. SHANG, H. BOLVARDI, Y. JIANG, A. AL GABAN, D. MUSIC, M. TO BABEN
SYMM 1.3	Thu	11:00–11:30	H 0105	Autonomous healing of crack damage in MAX phase ceramics — •WILLEM G. SLOOF
SYMM 1.4	Thu	11:30–12:00	H 0105	Magnetic MAX phases from first principles and thin film synthesis — •JOHANNA ROSEN
SYMM 1.5	Thu	12:00–12:30	H 0105	Weak Field Magneto-Transport Properties of Mn+1AXn Phases — •THIERRY OUISSE, LU SHI, BENOIT HACKENS, BENJAMIN PIOT, DIDIER CHAUSSENDE

Sessions

DS 1.1–1.14	Mon	9:30–13:00	H 2032	Organic Electronics and Photovoltaics
DS 2.1–2.13	Mon	9:30–13:00	H 0111	Thin Film Characterisation I: Structure Analysis and Composition
DS 3.1–3.15	Mon	15:00–19:30	H 2032	Organic Thin Films
DS 4.1–4.13	Mon	15:00–18:30	H 0111	Thin Film Characterisation II: Structure Analysis and Composition
DS 5.1–5.9	Mon	15:00–17:45	A 053	Transport: Topological Insulators 1 (joint session with DS, HL, MA, O)
DS 6.1–6.7	Mon	15:00–16:45	EW 202	Organic photovoltaics and electronics - mostly cell design (jointly with CPP,DS)
DS 7.1–7.8	Mon	17:00–19:00	EW 202	Organic photovoltaics and electronics - mostly properties of the absorber (jointly with CPP,DS)
DS 8.1–8.5	Mon	18:45–20:00	H 0111	Application of Thin Films
DS 9.1–9.7	Tue	9:30–13:00	H 2032	Focused Session: Doped Si nanostructures (joint session with HL)
DS 10.1–10.6	Tue	9:30–11:00	H 0111	Thermoelectric materials
DS 11.1–11.12	Tue	9:30–13:00	H 3005	Transport: Topological Insulators 2 (joint session with DS, HL, MA, O)
DS 12.1–12.10	Tue	9:30–12:15	A 053	Transport: Graphene (joint session with DS, DY, HL, MA, O)

DS 13.1–13.9	Tue	10:00–12:30	C 243	Interfaces and Thin Films I (joint session with CPP)
DS 14.1–14.11	Tue	10:30–13:15	MA 043	Plasmonics and nanooptics: Structure, fabrication and characterization (joint session with O)
DS 15.1–15.4	Tue	11:15–12:15	H 0111	High-k and Low-k Dielectrics (joint session with DF)
DS 16.1–16.3	Tue	12:15–13:00	H 0111	Atomic Layer Deposition
DS 17.1–17.8	Tue	14:00–16:00	H 0110	Transport: Topological Insulators 3 (joint session with DS, HL, MA, O)
DS 18.1–18.7	Tue	14:00–16:00	C 243	Interfaces and Thin Films II (joint session with CPP)
DS 19.1–19.9	Wed	9:30–12:15	H 2032	Ion and electron beam induced processes
DS 20.1–20.9	Wed	9:30–13:00	H 0111	Focussed Session: In-situ optical spectroscopy
DS 21.1–21.13	Wed	9:30–13:00	EB 107	Multiferroics I (joint session with DF)
DS 22.1–22.13	Wed	9:30–13:00	C 243	Interfaces and Thin Films III (joint session with CPP)
DS 23.1–23.8	Wed	9:30–11:30	ER 270	Topological insulators: Theory (HL with DS/MA/O/TT)
DS 24.1–24.9	Wed	10:30–12:45	MA 042	Metal substrates: Structure, epitaxy and growth (joint session with O)
DS 25.1–25.1	Wed	13:15–13:45	HE 101	GAEDE-PREIS 2015
DS 26.1–26.15	Wed	15:00–19:00	H 2032	Layer Properties: Electrical, Optical, and Mechanical Properties
DS 27.1–27.5	Wed	15:00–16:15	H 0111	Micro- and Nanopatterning
DS 28.1–28.13	Wed	15:00–18:50	EB 107	Multiferroics II (joint session with DF)
DS 29.1–29.13	Wed	15:00–18:15	MA 042	Oxide and insulator surface: Structure, epitaxy and growth (joint session with O)
DS 30.1–30.6	Wed	15:00–16:30	ER 270	Topological insulators: Structure and electronic structure (HL with DS/MA/O/TT)
DS 31.1–31.5	Wed	11:45–13:00	ER 270	Topological insulators: Transport (HL with DS/MA/O/TT)
DS 32.1–32.9	Wed	16:30–18:45	H 0111	Spins in organics
DS 33	Wed	19:00–20:00	H 0111	Mitgliederversammlung
DS 34.1–34.9	Thu	9:30–12:45	H 2032	Focussed Session: Oxide semiconductors I (joint session with HL)
DS 35.1–35.13	Thu	9:30–13:00	H 0111	Graphen
DS 36.1–36.110	Thu	9:30–12:00	Poster A	Poster Session I
DS 37.1–37.12	Thu	15:00–19:00	H 2032	Focussed Session: Oxide semiconductors II (joint session with HL)
DS 38.1–38.14	Thu	15:00–18:45	H 0111	Phase change/ resistive switching
DS 39.1–39.35	Thu	16:00–18:30	Poster F	Poster Session II
DS 40.1–40.13	Fri	9:30–13:15	H 2032	Metallic nanowires on the atomic scale (joint session with O)
DS 41.1–41.9	Fri	10:30–12:45	MA 042	Semiconductor substrates: structure, epitaxy and growth (joint session with O)

Annual General Meeting of the Thin Films Division

Wednesday 19:00–20:00 H 0111

- Bericht
- Wahl
- Verschiedenes